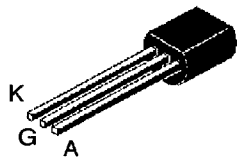
SGS-THOMSON MICROELECTRONICS

P01xxxA/B

SENSITIVE GATE SCR

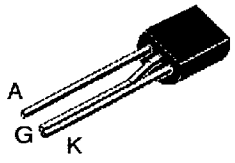
FEATURES

- $I_{T(RMS)}$ = 0.8A
- V_{DRM} = 100V to 400V
- Low I_{GT} < 1µA max to < 200µA



TO92
(Plastic)

P01xxxA



RD26
(Plastic)

P01xxxB

DESCRIPTION

The P01xxxA/B series of SCRs uses a high performance planar PNPN technology. These parts are intended for general purpose applications where low gate sensitivity is required.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	Tl= 55°C	0.8	A
$I_{T(AV)}$	Mean on-state current (180° conduction angle)	Tl= 55°C	0.5	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)	tp = 8.3 ms	8	A
		tp = 10 ms	7	
I^2t	I^2t Value for fusing	tp = 10 ms	0.24	A^2s
dI/dt	Critical rate of rise of on-state current I_G = 10 mA di_G/dt = 0.1 A/µs.		30	A/µs
T_{stg} T_j	Storage and operating junction temperature range		- 40, +150 - 40, +125	°C
Tl	Maximum lead temperature for soldering during 10s at 2mm from case		260	°C

Symbol	Parameter	Voltage				Unit
		A	B	C	D	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage T_j = 125°C R_{GK} = 1KΩ	100	200	300	400	V

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-a)	Junction to ambient	150	°C/W
Rth(j-l)	Junction to leads for DC	80	°C/W

GATE CHARACTERISTICS (maximum values)

$P_{G\ (AV)}$= 0.1 W P_{GM} = 2 W (tp = 20 µs) I_{GM} = 1 A (tp = 20 µs)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Sensitivity					Unit
				02	09	11	15	18	
I_{GT}	V_D=12V (DC) R_L=140Ω	Tj= 25°C	MIN			4	15	0.5	µA
			MAX	200	1	25	50	5	
V_{GT}	V_D=12V (DC) R_L=140Ω	Tj= 25°C	MAX	0.8					V
V_{GD}	V_D=V_{DRM} R_L=3.3kΩ R_{GK} = 1 KΩ	Tj= 125°C	MIN	0.1					V
V_{RGM}	I_{RG} =10µA	Tj= 25°C	MIN	8					V
tgd	V_D=V_{DRM} I_{TM}= 3 x $I_{T(AV)}$ dI_G/dt = 0.1A/µs I_G = 10mA	Tj= 25°C	TYP	0.5					µs
I_H	I_T= 50mA R_{GK} = 1 KΩ	Tj= 25°C	MAX	5					mA
I_L	I_G=1mA R_{GK} = 1 KΩ	Tj= 25°C	MAX	6					mA
V_{TM}	I_{TM}= 1.6A tp= 380µs	Tj= 25°C	MAX	1.93					V
I_{DRM} I_{RRM}	V_D = V_{DRM} R_{GK} = 1 KΩ V_R = V_{RRM}	Tj= 25°C	MAX	1					µA
		Tj= 125°C	MAX	100					µA
dV/dt	V_D=67%V_{DRM} R_{GK} = 1 KΩ	Tj= 125°C	MIN	25	25	50	100	30	V/µs
tq	I_{TM}= 3 x $I_{T(AV)}$ V_R=35V dI/dt=10A/µs tp=100µs dV/dt=10V/µs V_D= 67%V_{DRM} R_{GK} = 1 KΩ	Tj= 125°C	MAX	200					µs

ORDERING INFORMATION

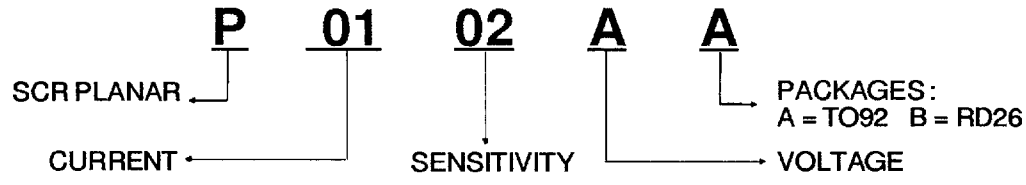


Fig.1 : Maximum average power dissipation versus average on-state current.

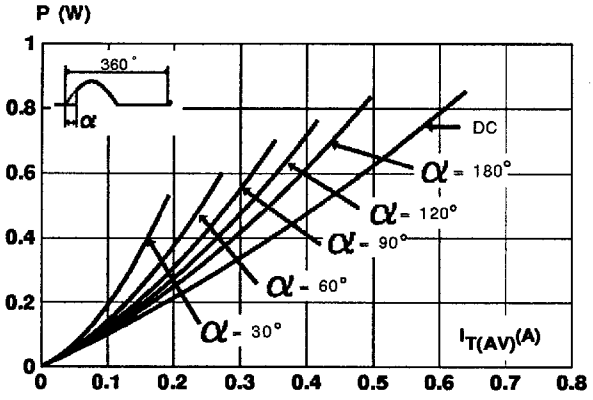


Fig.2 : Correlation between maximum average power dissipation and maximum allowable temperature (Tamb and Tlead).

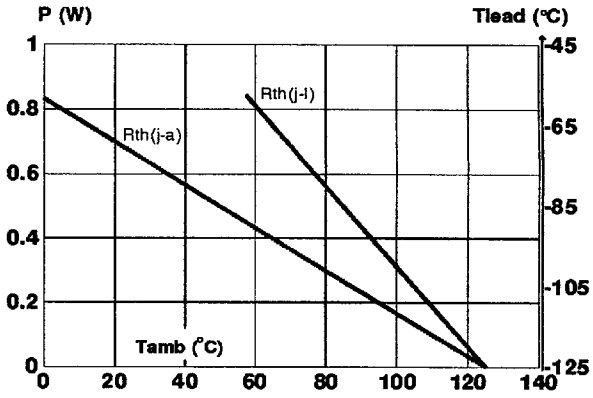


Fig.3 : Average on-state current versus lead temperature.

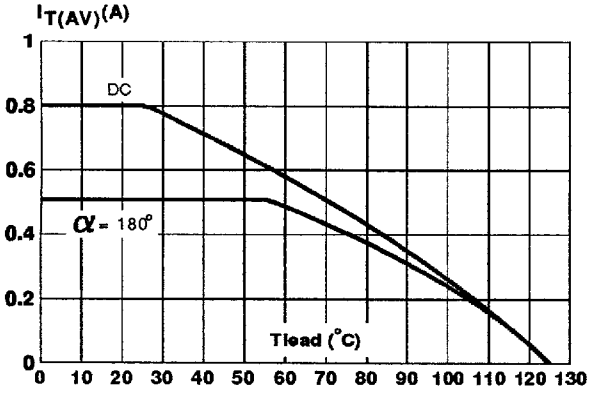


Fig.4 : Relative variation of thermal impedance junction to ambient versus pulse duration.

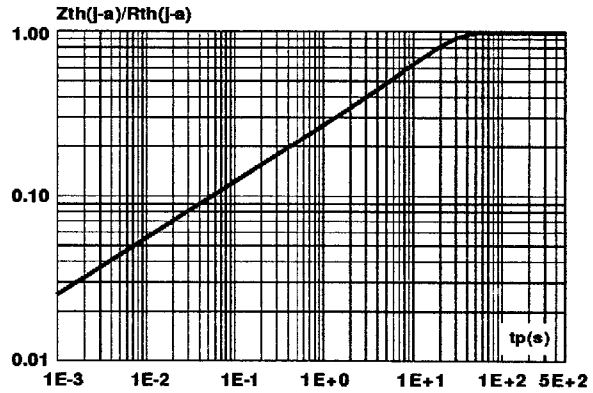


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

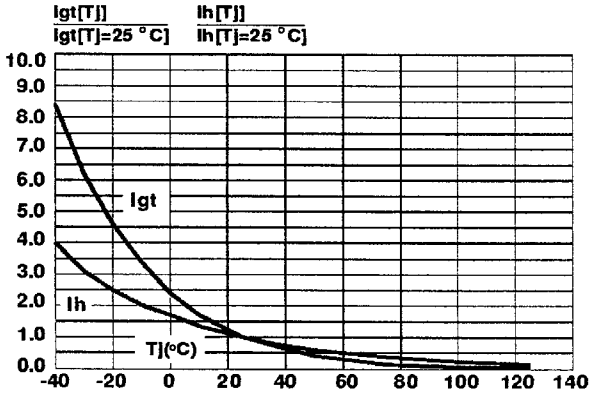


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.

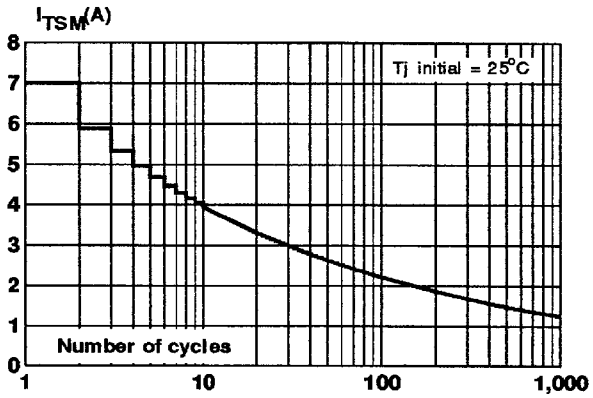


Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : tp ≤ 10ms, and corresponding value of I^2t.

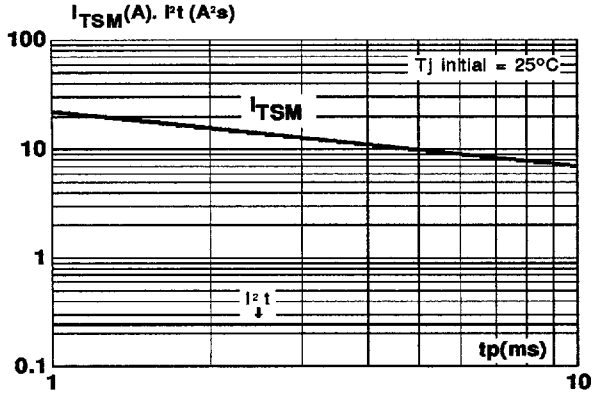


Fig.8 : On-state characteristics (maximum values).

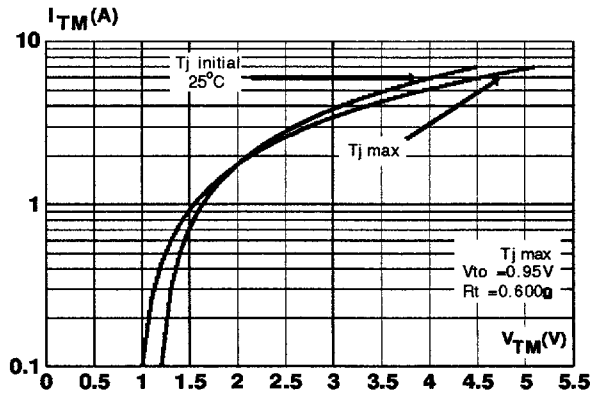
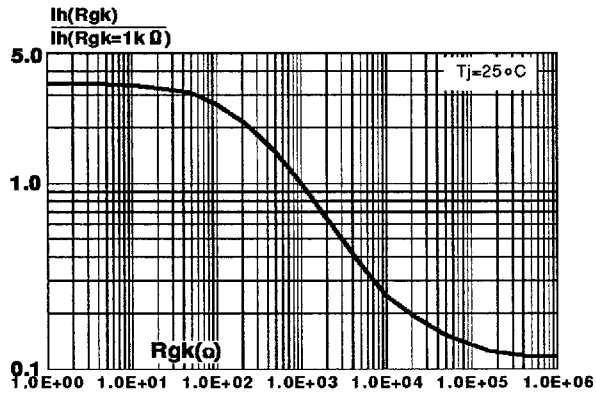
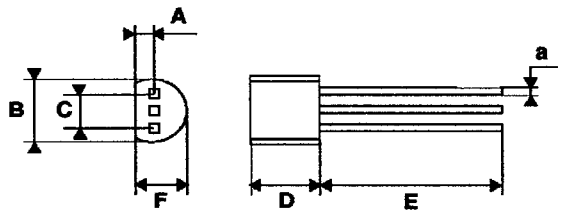


Fig.9 : Relative variation of holding current versus gate-cathode resistance (typical values).



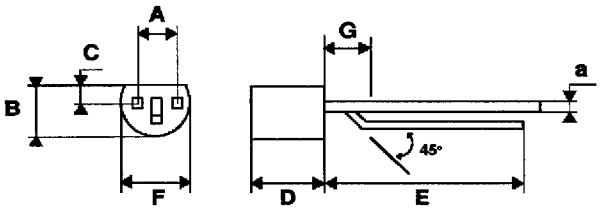
PACKAGE MECHANICAL DATA
TO92 (Plastic)



REF.	DIMENSIONS					
	Millimeters			Inches		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A	1.35			0.053		
B			4.7			0.185
C	2.54			0.100		
D		4.4	4.8		0.173	0.189
E		12.7			0.500	
F			3.7			0.146
a			0.45			0.017

Marking : type number
Weight : 0.2 g

PACKAGE MECHANICAL DATA
RD26 (Plastic)



REF.	DIMENSIONS					
	Millimeters			Inches		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A	2.54			0.100		
B			3.7			0.146
C	1.35			0.053		
D		4.4	4.8		0.173	0.189
E		12.7			0.500	
F			4.7			0.185
G			3.0			0.118
a			0.45			0.177

Marking : type number
Weight : 0.2 g